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Fax Number: (703) 872-9319 Telephone No.: (703) 872-9317  
From: Bradley J. Berezna (Reg. No. 33,474)  
Date: July 05, 2002 Time: 11:00 a.m. PDT  
Operator: Caitlin Burgess Matter: 003692.P007XD  
Number of pages including cover sheet: 10  
In Re Patent Application of: Rumennik, et al.  
Application No.: 09/574,563 Filed: May 17, 2000  
For: High-Voltage Transistor With Multi-layer Conduction Region

Enclosed are the following documents: Amendment and Response After Final Office Action.  
Please call Bradley J. Berezna, should you have any questions regarding the above.

Respectfully Submitted.

Bradley J. Berezna

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(Rev. 11/23/97)

Attorney Docket No. 03692.P007XD

**AMENDMENT UNDER  
37 C.F.R. § 1.116  
EXPEDITED PROCEDURE  
EXAMINING GROUP 2811****PATENT****IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of:

***RUMENNIK, et al.***

Serial No.: 09/574,563 ✓

Filing Date: May 17, 2000 ✓

For: HIGH-VOLTAGE TRANSISTOR WITH  
MULTI-LAYER CONDUCTION REGION

Examiner: Hu, S.

Art Unit: 2811

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**Amendment and Response After Final Office Action**Hon. Commissioner of Patents and Trademarks  
Washington, D.C. 20231

Sir:

In response to the Final Office Action mailed May 31, 2002, Applicants respectfully request the following amendments be entered and the following remarks be considered:

**In The Claims:**

Claim 104 should be replaced with:

104. (Amended) The HVFET according to claim 1 wherein the buried region has a doped impurity concentration approximately twice that of the first conduction channel.